



01PSE00-114BD

February 10, 2004

To: Commissioner for Patents
P.O. Box 1450
Alexandria, VA 22313-1450

Fr: George O. Saile, Reg. No. 19,572
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Subject:

Serial No. 10/736,943 12/16/03

Wenhe Lin et al.

METHODS TO FORM DUAL METAL GATES
BY INCORPORATING METALS AND THEIR
CONDUCTIVE OXIDES

INFORMATION DISCLOSURE STATEMENT

Enclosed is Form PTO-1449, Information Disclosure Citation
In An Application.

The following Patents and/or Publications are submitted to
comply with the duty of disclosure under CFR 1.97-1.99 and
37 CFR 1.56.

CERTIFICATE OF MAILING

I hereby certify that this correspondence is being
deposited with the United States Postal Service as first class
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P.O. Box 1450, Alexandria, VA 22313-1450, on February , 2004.

Stephen B. Ackerman, Reg.# 37761

Signature/Date Steph B Ackerman 2/12/04

CS-00-114BD

U.S. Patent 6,043,157 to Gardner et al., "Semiconductor Device Having Dual Gate Electrode Material and Process of Fabrication Thereof," discloses a process for forming dual gates where one gate is polysilicon and the other gate is metal.

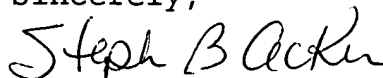
U.S. Patent 6,087,231 to Xiang et al., "Fabrication of Dual Gates of Field Transistors with Prevention of Reaction Between the Gate Electrode and the Gate Dielectric with a High Dielectric Constant," discloses a dummy gate process where amorphous gates doped with different dopants are formed.

U.S. Patent 6,083,836 to Rodder, "Transistors with Substitutionally Formed Gate Structures and Method," teaches a dummy gate process where two gates are formed.

U.S. Patent 5,266,519 to Iwamoto, "Method for Forming a Metal Conductor in Semiconductor Device," teaches oxidation of a metal film to be used as an anti-plating mask.

U.S. Patent Application CS-00-115, Serial #09/981,415, filed on 10/18/01, assigned to the same assignee, now issued as U.S. 6,475,908, describes methods for forming dual-metal gate CMOS transistors.

Sincerely,



Stephen B. Ackerman, Reg. #37761

Form PTO-1449

INFORMATION DISCLOSURE CITATION
OF AN APPLICATION

FEB 17 2004

(Use several sheets if necessary)

Docket Number (Optional)

CS-00-1148D

Application Number

10/736,943

Applicant

Wenhe Lin et al.

Filing Date

12/16/03

Group Art Unit

U. S. PATENT DOCUMENTS

EXAMINER INITIAL	DOCUMENT NUMBER	DATE	NAME	CLASS	SUBCLASS	PLNDG DATE & APPROPRIATE
	6043157	3/28/00	Gardner et al.	438	692	12/18/97
	6087231	7/11/00	Xiang et al.	438	287	8/5/99
	6083836	7/4/00	Rodder	438	690	12/18/98
	5266519	11/30/93	Iwamoto	437	183	11/12/92

FOREIGN PATENT DOCUMENTS

DOCUMENT NUMBER	DATE	COUNTRY	CLASS	SUBCLASS	Translation	
					YES	NO

OTHER DOCUMENTS (Including Author, Title, Date, Portion of Pages, Etc.)

	U.S. Patent App. CS-00-115, Serial #09/981,415, filed on 10/18/01, same assignee, now issued US 6,475,908, date of Patent 11/5/02, US Class 438/659.

EXAMINER

DATE CONSIDERED

EXAMINER: Initial if citation considered, whether or not citation is in conformance with MPEP § 609; Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to the applicant.